MOSFETs Silicon N-Channel MOS (DTMOS V)

TK560A65Y

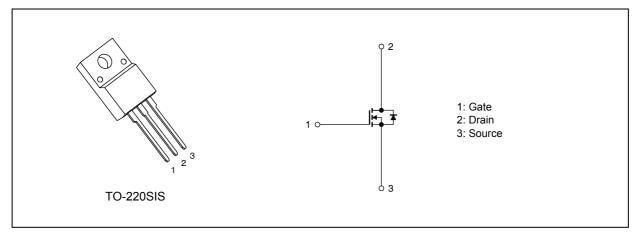
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.43 \Omega$ (typ.) by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 3 to 4 V (V_{DS} = 10 V, I_D = 0.24mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \,^{\circ}C$ unless otherwise specified)

Characteris	stics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	650	V
Gate-source voltage			V _{GSS}	±30	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	Ι _D	7	A
Drain current (DC)	(T _c = 100 °C)	(Note 1)	Ι _D	4.4	A
Drain current (pulsed)	(T _c = 25 °C)	(Note 1)	I _{DP}	28	A
Power dissipation	(T _c = 25 °C)		PD	30	W
Single-pulse avalanche energy		(Note 2)	E _{AS}	59	mJ
Single-pulse avalanche current			I _{AS}	1.8	A
Reverse drain current (DC)		(Note 1)	I _{DR}	7	
Reverse drain current (pulsed)		(Note 1)	I _{DRP}	28	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	°C
Isolation voltage (RMS)	(t = 1.0 s)		V _{ISO(RMS)}	2000	V
Mounting torque			TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2016-12

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	4.16	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 32.5 mH, R_G = 25 Ω , I_{AS} = 1.8 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 650 V, V_{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.24 mA	3	_	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.5 A	_	0.43	0.56	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V_{DS} = 300 V, V_{GS} = 0 V, f = 100 kHz	_	380	—	pF
Reverse transfer capacitance	C _{rss}		_	2.5	_	
Output capacitance	C _{oss}		_	18	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	30	_	
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz	_	32	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	20	_	ns
Switching time (turn-on time)	t _{on}		_	50	_	
Switching time (fall time)	t _f		_	8	_	
Switching time (turn-off time)	t _{off}			105	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \leq V_{(BR)DSS}, \ I_D \leq 3.5 \ A$	50	_	_	V/ns

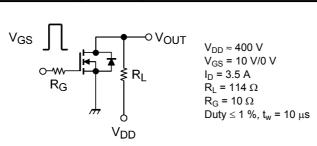


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 7 A		14.5	_	nC
Gate-source charge 1	Q _{gs1}		_	2.3	_	
Gate-drain charge	Q _{gd}			7.5		

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 7 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$V_{DD} \approx 400 \text{ V}$	_	240	_	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 3 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs		1.6	_	μC
Peak reverse recovery current	l _{rr}		_	14.2	_	А
Diode dv/dt ruggedness	dv/dt	$V_{DS} \leq 400$ V, $I_{DR} \leq 3$ A, V_{GS} = 0 V	15	_	_	V/ns

7. Marking (Note)

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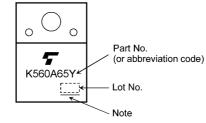
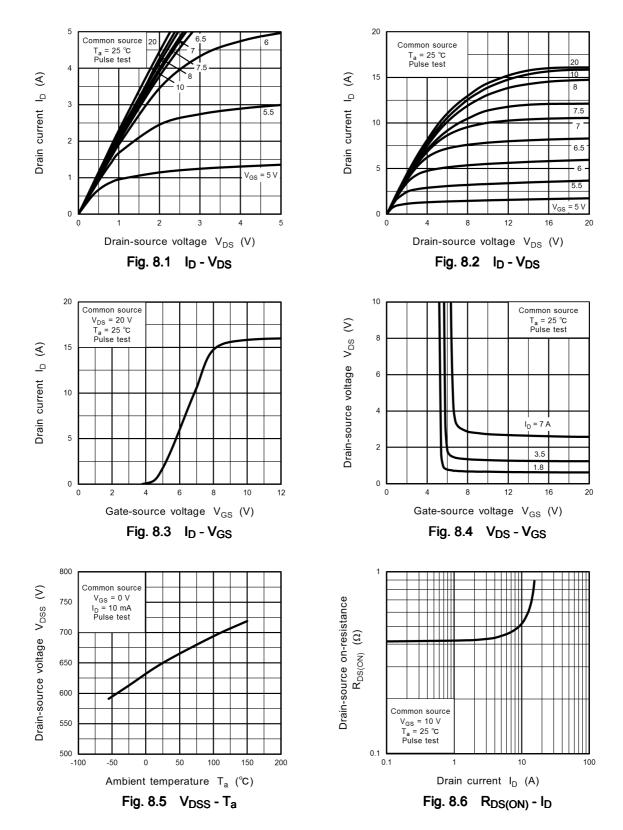


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]] Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)



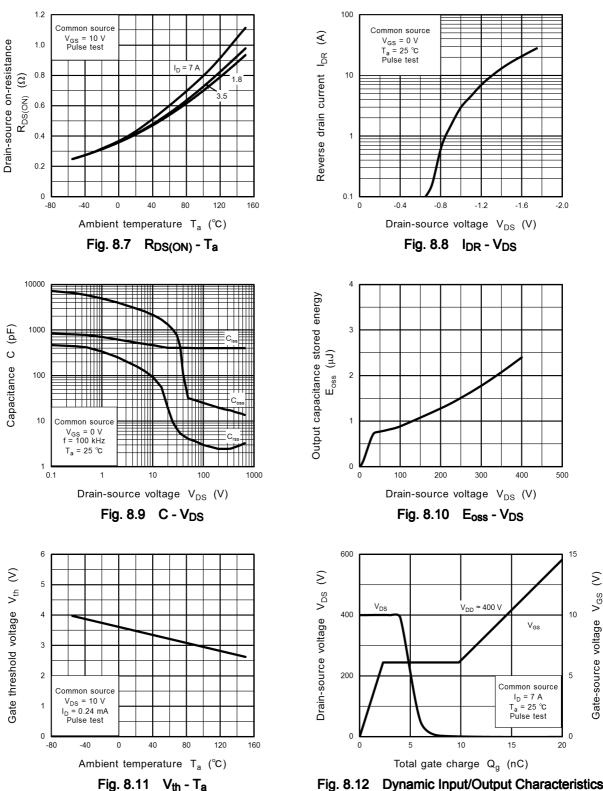


Fig. 8.12 Dynamic Input/Output Characteristics

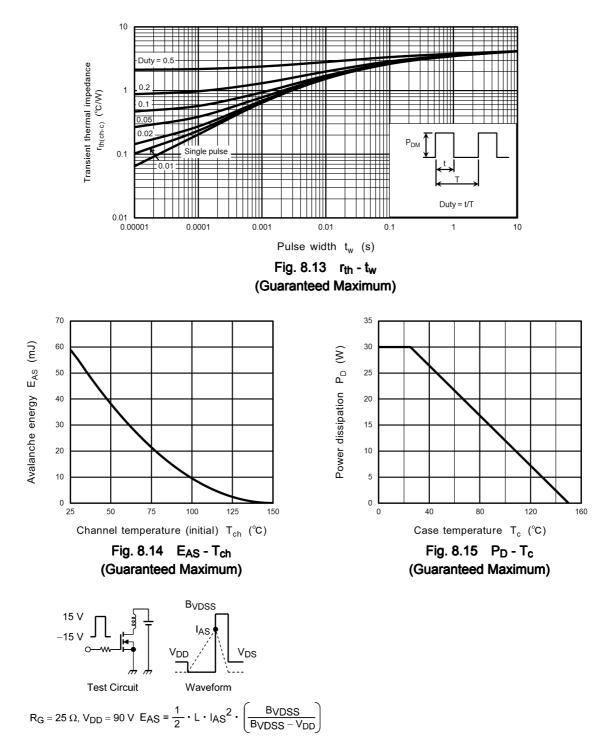
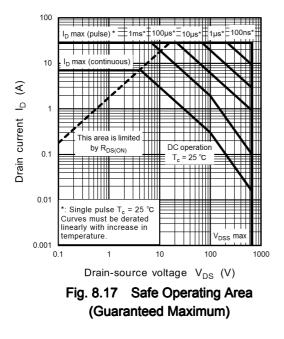


Fig. 8.16 Test Circuit/Waveform

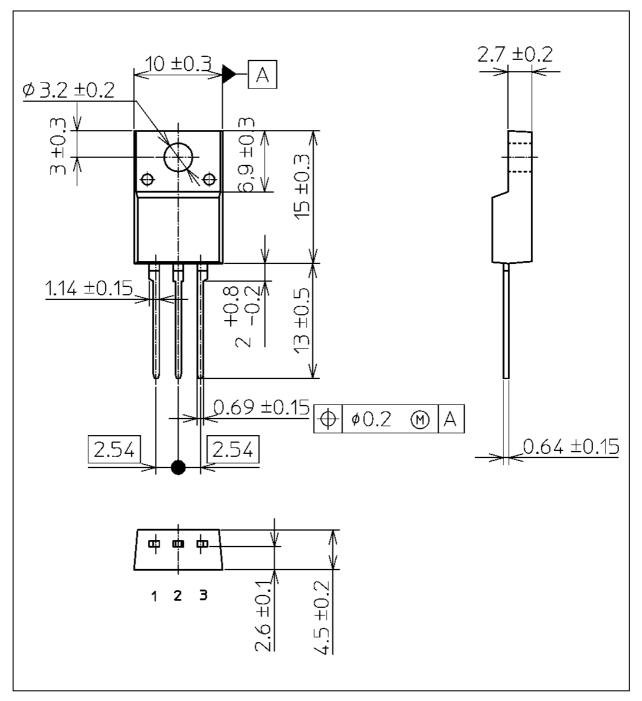


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

TK560A65Y

Unit: mm



Weight: 1.7 g (typ.)

	Package Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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